

# Central<sup>TM</sup> Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA  
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

2N2646  
2N2647

SILICON UNIJUNCTION TRANSISTOR

JEDEC TO-18 CASE\*

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N2646, 2N2647 types are silicon PN unijunction transistors designed for general purpose industrial applications.

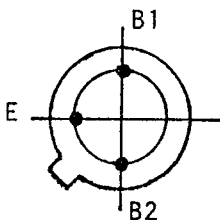
MAXIMUM RATINGS (TA=25°C unless otherwise noted)

	<u>SYMBOL</u>		<u>UNIT</u>
RMS Power Dissipation	PD (RMS)	300	mW
RMS Emitter Current	IE (RMS)	50	mA
Peak Pulse Emitter Current	iE	2.0	A
Interbase Voltage	VB2B1	35	V
Emitter Reverse Voltage	VB2E	30	V
Operating and Storage Junction Temperature	TJ, TSTG	-65 TO +150	°C

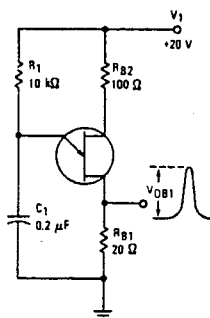
ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	2N2646		2N2647		<u>UNIT</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
η	VB2B1=10V†	0.56	0.75	0.68	0.82	-
RBBO	VB2B1=3.0V, IE=0	4.7	9.1	4.7	9.1	kΩ
IB2(MOD)	VB2B1=10V, IE=50mA	15 TYP		15 TYP		mA
αRBBO	VB2B1=3.0V, TA=-65°C to +150°C	0.1	0.9	0.1	0.9	%/°C
VEB1(SAT)	VB2B1=10V, IE=50mA	3.5 TYP		3.5 TYP		V
IEO	VB2E=30V, IB1=0		12		0.2	μA
IP	VB2B1=25V		5.0		2.0	μA
IV	VB2B1=20V, RB2=100Ω	4.0	-	8.0	18	mA
VOB1	See test circuit below	3.0		6.0		V

\*Conforms to JEDEC TO-18 outline except for lead configuration.



VOB1 TEST CIRCUIT



†η TEST CIRCUIT

